

# CNA1301H

## Photo Interrupter

For contactless SW, object detection

### ■ Overview

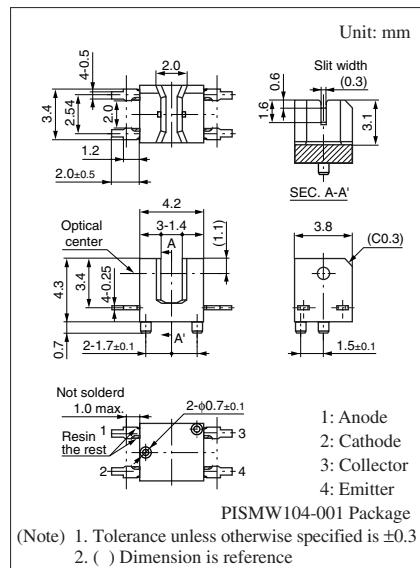
CNA1301H is an ultraminiature, highly reliable transmissive photosensor in which a high efficiency GaAs infrared light emitting diode chip and a high sensitivity Si phototransistor chip are integrated in a double molded resin package.

### ■ Features

- Ultraminiature: 3.8 mm × 4.2 mm (height: 4.3 mm)
- Highly precise position detection: 0.15 mm
- Gap width: 1.4 mm
- Support for thin equipment (permits direct mounting on printed circuit board)

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Input (Light emitting diode)	Reverse voltage	$V_R$	6 V
	Forward current	$I_F$	50 mA
	Power dissipation <sup>*1</sup>	$P_D$	75 mW
Output (Photo transistor)	Collector-emitter voltage (Base open)	$V_{CEO}$	35 V
	Emitter-collector voltage (Base open)	$V_{ECO}$	6 V
	Collector current	$I_C$	20 mA
	Collector power dissipation <sup>*2</sup>	$P_C$	75 mW
Temperature	Operating ambient temperature	$T_{opr}$	-25 to +85 $^\circ\text{C}$
	Storage temperature	$T_{stg}$	-40 to +100 $^\circ\text{C}$



(Note) 1. Tolerance unless otherwise specified is  $\pm 0.3$   
2. ( ) Dimension is reference

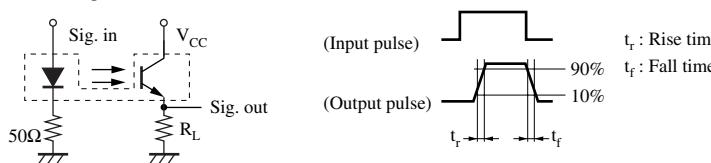
### ■ Electrical-Optical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

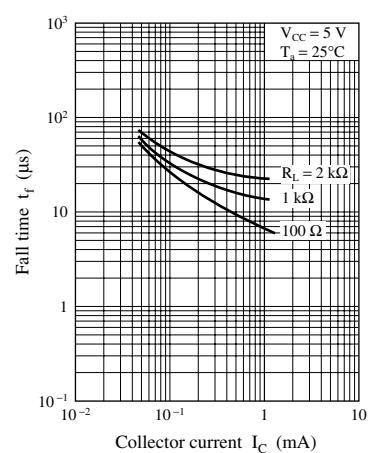
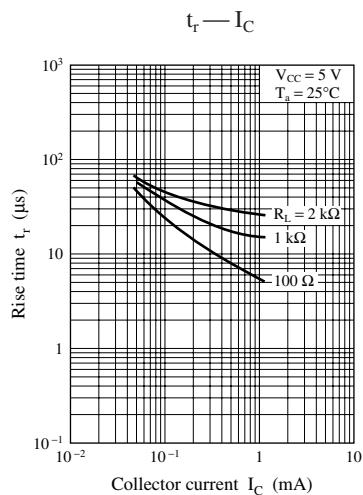
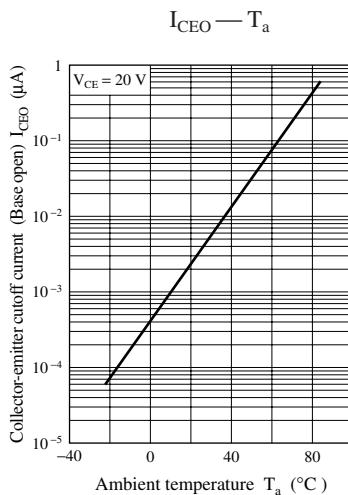
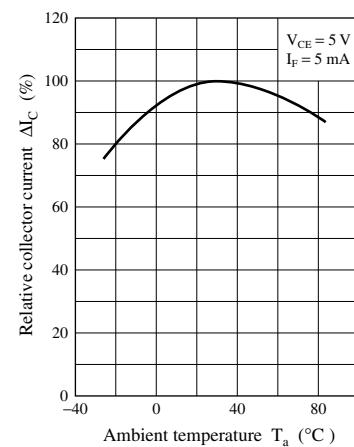
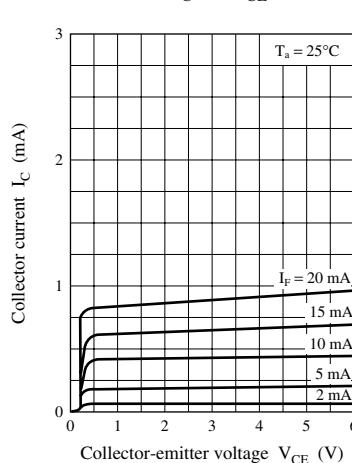
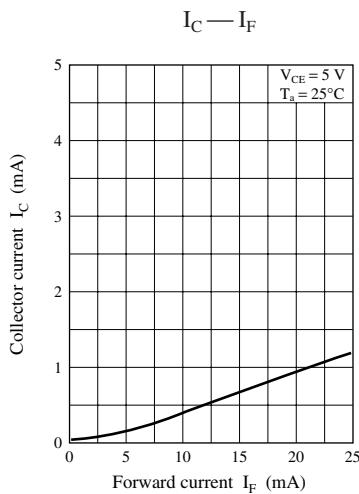
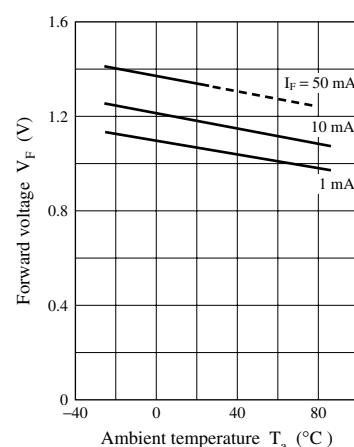
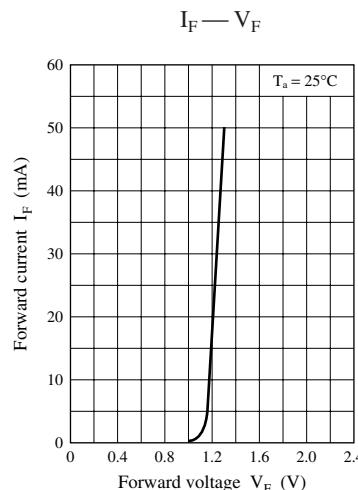
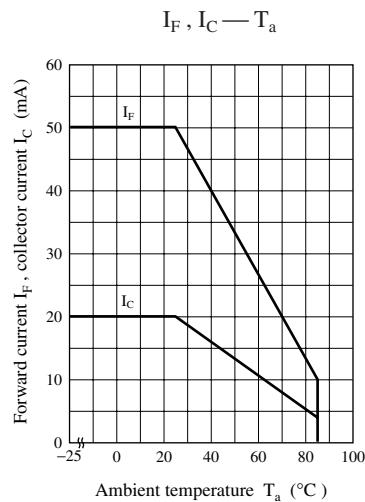
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input characteristics	Forward voltage	$V_F$	$I_F = 20 \text{ mA}$		1.2	1.4 V
	Reverse current	$I_R$	$V_R = 3 \text{ V}$			10 $\mu\text{A}$
Output characteristics	Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 20 \text{ V}$			100 nA
Transfer characteristics	Collector current	$I_C$	$V_{CE} = 5 \text{ V}$ , $I_F = 5 \text{ mA}$	100		1300 $\mu\text{A}$
	Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_F = 10 \text{ mA}$ , $I_C = 50 \mu\text{A}$			0.4 V
	Rise time <sup>*</sup>	$t_r$	$V_{CC} = 5 \text{ V}$ , $I_C = 0.1 \text{ mA}$		35	$\mu\text{s}$
	Fall time <sup>*</sup>	$t_f$	$R_L = 1000 \Omega$		35	$\mu\text{s}$

Note) 1. Input and output are practiced by electricity.

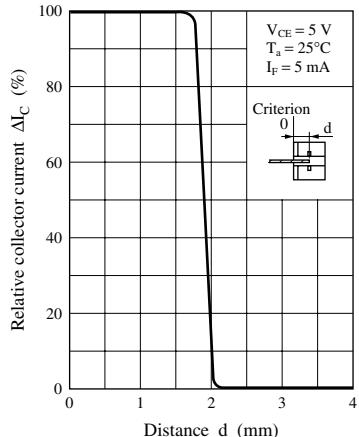
2. This device is designed be disregarded radiation.

3. <sup>\*</sup>: Switching time measurement circuit

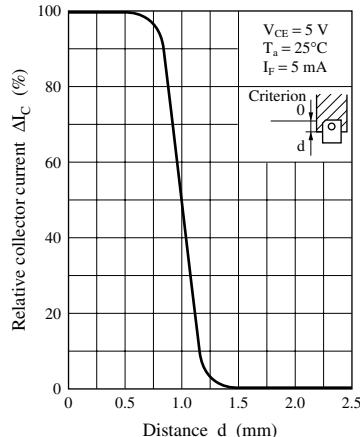




$\Delta I_C - d$  (1)



$\Delta I_C - d$  (2)



# ⚠ Caution for Safety

## ⚠ DANGER

### ■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.

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(2) The technical information described in this material is limited to showing representative characteristics and applied circuits examples of the products. It neither warrants non-infringement of intellectual property right or any other rights owned by our company or a third party, nor grants any license.

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